N- and P-Channel 30-V (D-S) MOSFET

CHARACTERISTICS

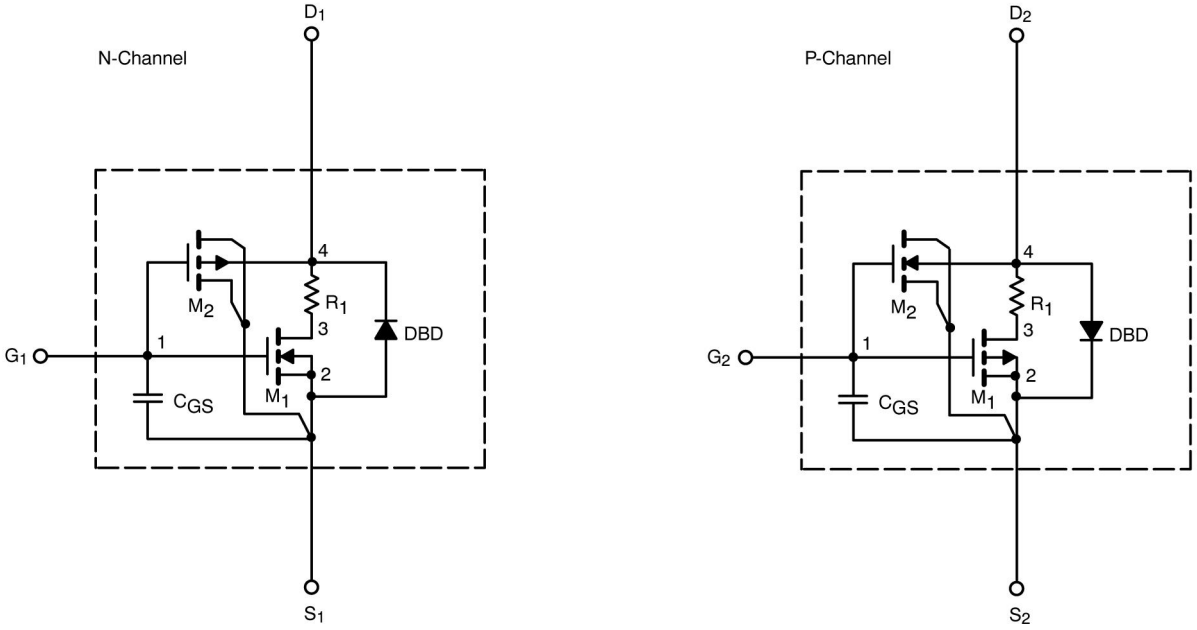
- N- and P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the –55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n- and p-channel vertical DMOS. The subcircuit model is extracted and optimized over the –55 to 125°C temperature ranges under the pulsed 0 to 10V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC



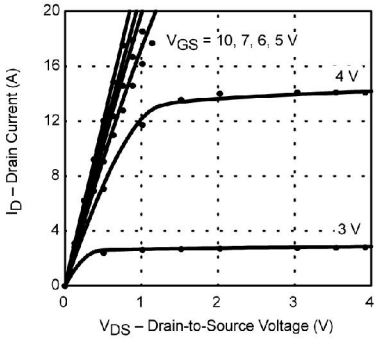
This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

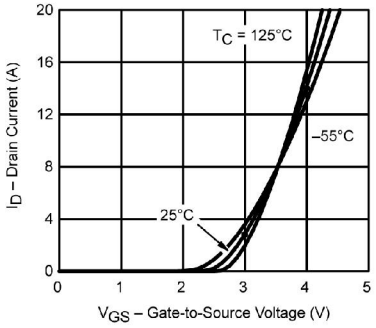
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**		**Simulated Data**	**Measured Data**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	N-Ch	1.8		V
		V_{DS} = V_{GS}, I_D = –250 µA	P-Ch	2.2		
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	N-Ch	110		A
		V_{DS} ≤ –5 V, V_{GS} = –10 V	P-Ch	62		
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 4.9 A	N-Ch	0.042	0.044	Ω
		V_{GS} = –10 V, I_D = –3.9 A	P-Ch	0.071	0.062	
		V_{GS} = 4.5 V, I_D = 4.1 A	N-Ch	0.057	0.062	
		V_{GS} = –4.5 V, I_D = –3 A	P-Ch	0.120	0.105	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 4.9 A	N-Ch	9.2	11	S
		V_{DS} = –15 V, I_D = –2.5 A	P-Ch	5	5	
Diode Forward Voltage[a]	V_{SD}	I_S = 1.7 A, V_{GS} = 0 V	N-Ch	0.70	0.80	V
		I_S = –1.7 A, V_{GS} = 0 V	P-Ch	–0.80	–0.82	
Dynamic[b]						
Total Gate Charge	Q_g	N-Channel V_{DS} = 10 V, V_{GS} = 10 V, I_D = 4.9 A P-Channel V_{DS} = –10 V, V_{GS} = –10 V, I_D = –3.9 A	N-Ch	7.4	8	Nc
			P-Ch	9.6	10	
Gate-Source Charge	Q_{gs}		N-Ch	1.4	1.4	
			P-Ch	2	2	
Gate-Drain Charge	Q_{gd}		N-Ch	1.2	1.2	
			P-Ch	1.9	1.9	
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} =10 V, R_L = 10 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_G = 6 Ω P-Channel V_{DD} = –10 V, R_L = 10 Ω I_D ≅ –1 A, V_{GEN} = –10 V, R_G = 6 Ω	N-Ch	8	12	Ns
			P-Ch	12	8	
Rise Time	t_r		N-Ch	10	10	
			P-Ch	14	9	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch	13	23	
			P-Ch	16	21	
Fall Time	t_f		N-Ch	17	8	
			P-Ch	22	10	
Source-Drain Reverse Recovery Time	t_{rr}	I_S = 1.7 A, di/dt = 100 A/µs	N-Ch	24	25	
		I_S = –1.7 A, di/dt = 100 A/µs	P-Ch	30	27	

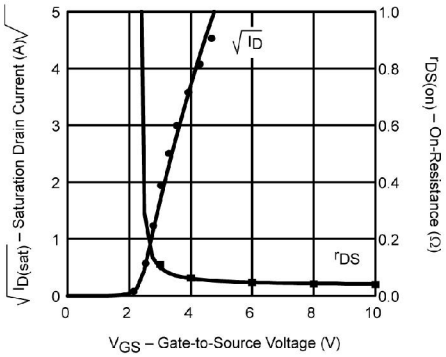
Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2.
b. Guaranteed by design, not subject to production testing.

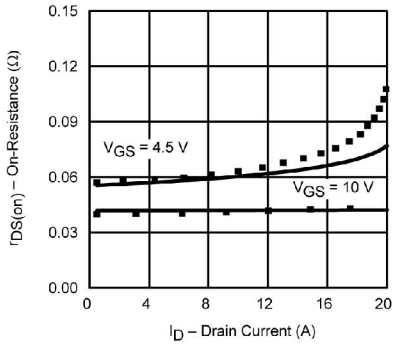
COMPARISON OF MODEL WITH MEASURED DATA (T_J=25°C UNLESS OTHERWISE NOTED)

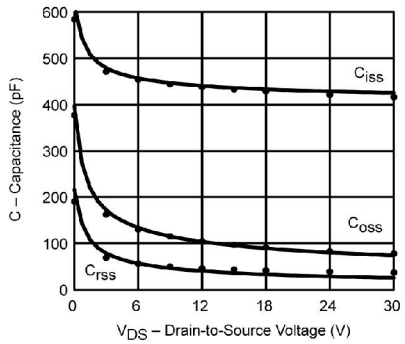
N-Channel MOSFET

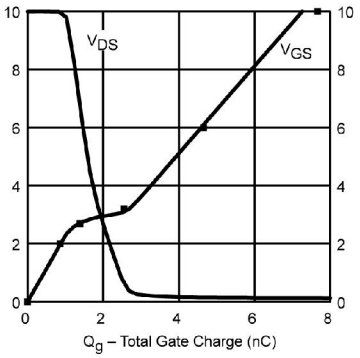






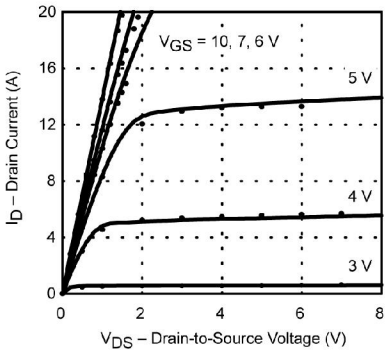


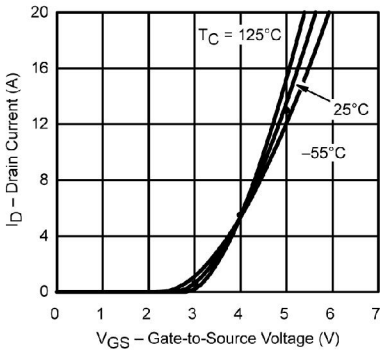


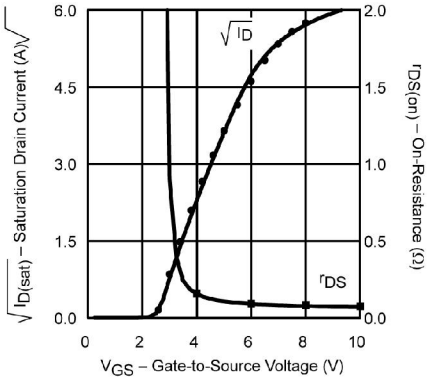


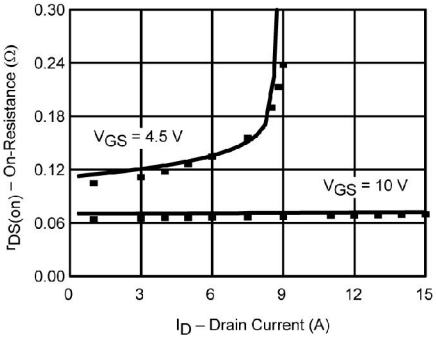
Note: Dots and squares represent measured data.

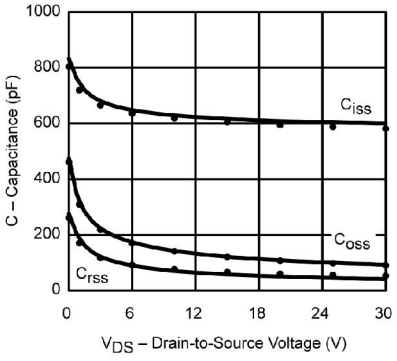
P-Channel MOSFET

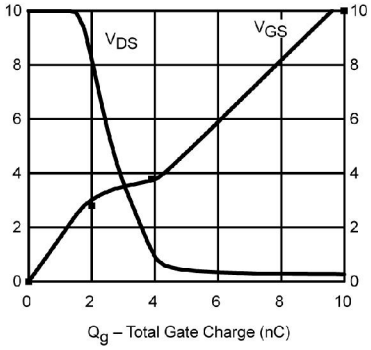












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